

GP 2822



**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Leonard Forbes  
Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH  
Docket No.: 303.229US2 Serial No.: 09/132,157  
Filed: August 11, 1998 Due Date: October 18, 2000  
Examiner: Mark V. Prenty Group Art Unit: 2822

Commissioner for Patents  
Washington, D.C. 20231

We are transmitting herewith the following attached items (as indicated with an "X"):

A return postcard.  
 An Amendment and Response (8 Pages).

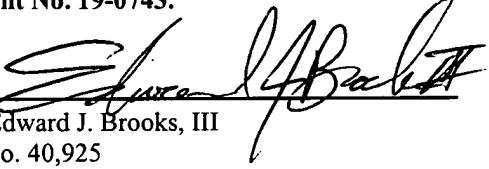
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OCT 25 2000

TECHNOLOGY CENTER 2800

Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
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**CERTIFICATE UNDER 37 CFR 1.8:** The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on this 18 day of October, 2000.

Name

Amy Moriarty

Signature

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*#3016  
10-26-00  
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S/N 09/132,157

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Leonard Forbes

Examiner: Mark V. Prenty

Serial No.: 09/132,157

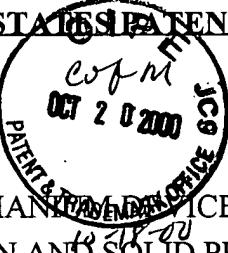
Group Art Unit: 2822

Filed: August 11, 1998

Docket: 303.229US2

Title:

SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION  
IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH



**AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111**

Commissioner for Patents  
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on July 18, 2000. Please amend the above-identified patent application as follows.

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**IN THE CLAIMS**

OCT 25 2000

*TECHNOLOGY CENTER 2800*

Please amend the claims as follows:

*Sub H*

11. (Four times amended) A p-channel metal-oxide-semiconductor transistor, comprising:  
a silicon substrate;  
a gate oxide, coupled to the substrate;  
a gate, coupled to the gate oxide;  
source/drain regions formed in the substrate on opposite sides of the gate; and  
a  $Si_{1-x}Ge_x$  channel region, having a germanium molar fraction of x, and formed in the substrate, underneath and adjoining the gate oxide and between the source/drain regions;  
wherein the  $Si_{1-x}Ge_x$  channel region [is formed subsequent to formation of the gate oxide.] has a channel length less than 7  $\mu m$ .

*G1*

*Sub J*

24. (Four times amended) A p-channel metal-oxide-semiconductor transistor formed on a silicon substrate, comprising:  
a  $Si_{1-x}Ge_x$  channel region, having a germanium molar fraction of x, and formed in the substrate, underneath and adjoining a gate oxide and between a source region and a drain region;

*G2*